

*CLAIM AMENDMENTS*

1. (Currently Amended) A semiconductor integrated circuit device comprising:  
a resonant circuit ~~which makes resonance~~ resonating at an arbitrary frequency;  
a transmission line for transmitting a high-frequency signal having said frequency,  
~~one of two wherein a first end portions~~ of said transmission line being connected to said  
resonant circuit;

an active element having a first electrode connected to ~~the other~~ a second end  
~~portion~~ of said transmission line, a second electrode which is grounded through a reactance  
element, and a third electrode;

an output-matching circuit including a diode section for regulating an oscillation  
power and a high-frequency signal output terminal, ~~one of two wherein a first end portions~~  
of said diode section being is connected to said third electrode of said active element, and said  
high-frequency signal output terminal being is connected to ~~the other~~ a second end portion of  
said diode section; and

a substrate having a main surface on which said resonant circuit, said transmission  
line, said active element and said output-matching circuit are arranged.

2. (Currently Amended) The semiconductor integrated circuit device according to  
claim 1, wherein said diode section includes a plurality of diodes ~~arranged in~~ having an  
inverse parallel ~~manner~~ arrangement.

3. (Original) The semiconductor integrated circuit device according to claim 1,  
wherein said diode section includes a plurality of diodes arranged in series.

4. (Original) The semiconductor integrated circuit device according to claim 1,  
further comprising a bias circuit for applying a DC bias to said diode section.

5. (Currently Amended) A semiconductor integrated circuit device comprising:  
a resonant circuit ~~which makes resonance~~ resonating at an arbitrary frequency;  
a transmission line for transmitting a high-frequency signal having said frequency,  
~~one of two wherein a first end portions~~ of said transmission line being connected to said  
resonant circuit;

an oscillation power regulating circuit including a diode section for regulating an  
oscillation power, ~~one end portion of wherein~~ said oscillation power regulating circuit being  
is connected to ~~the other~~ a second end portion of said transmission line;

an active element having a first electrode connected to the ~~other~~ second end portion of said transmission line, a second electrode which is grounded through a reactance element, and a third electrode;

an output-matching circuit including a high-frequency signal output terminal, wherein said output-matching circuit ~~being~~ is connected to said third electrode of said active element; and

a substrate having a main surface on which said resonant circuit, said transmission line, said oscillation power regulating circuit, said active element and said output-matching circuit are arranged.

6. (Currently Amended) The semiconductor integrated circuit device according to claim 5, wherein said diode section includes a plurality of diodes ~~arranged in~~ having an inverse parallel ~~manner~~ arrangement.

7. (Original) The semiconductor integrated circuit device according to claim 5, wherein said diode section includes a plurality of diodes arranged in series.

8. (Original) The semiconductor integrated circuit device according to claim 5, further comprising a bias circuit for applying a DC bias to said diode section.